

MSM521209

131,072-Word × 9-Bit CMOS STATIC RAM

DESCRIPTION

The MSM521209 is a 131,072-word by 9-bit CMOS fast static RAM featuring a single 3.3 V power supply operation and direct LVTTL input/output compatibility. Since the circuitry is completely static, external clock and refreshing operations are unnecessary, making this device very easy to use. The MSM521209 can be used in the high-speed operation of an access time 20 ns due to adopting a high-performance CMOS technology. In addition, the MSM521209 is provided with a chip enable signal (\overline{CE}) suited to the power-down function, and an output enable signal (\overline{OE}) suited to the I/O bus line control.

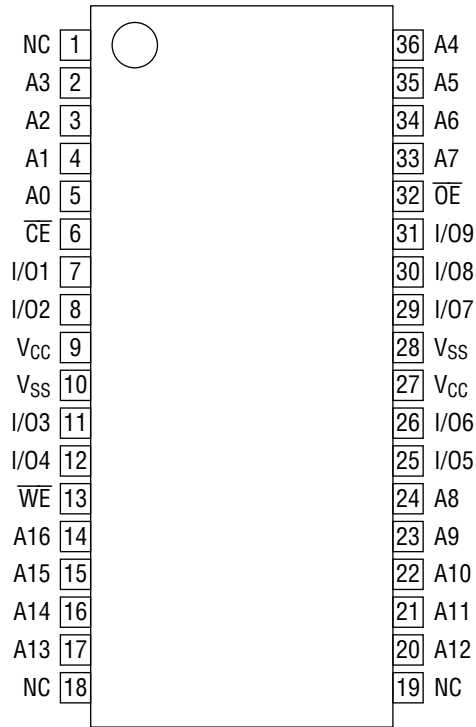
FEATURES

- 131,072-word × 9-bit configuration
- Single 3.3 V power supply
- Fully static operation
- Operating temperature range: Ta = 0°C to 70°C
- Power dissipation
 - Standby: 2 mA (Max.)
 - Operation:
 - 20 200 mA (Max.)
 - 25 180 mA (Max.)
 - 30 160 mA (Max.)
- Access time:
 - 20 20 ns (Max.)
 - 25 25 ns (Max.)
 - 30 30 ns (Max.)
- (Input/Output) LVTTL compatible
- Power-down function by chip enable signal
- 3-state output
- Package:
 - 36-pin 400 mil plastic SOJ (SOJ36-P-400-1.27) (Product : MSM521209-xxJS)
xx indicates speed rank.

PRODUCT FAMILY

Family	Access Time (Max.)	Package
MSM521209-20	20 ns	400 mil 36-pin SOJ
MSM521209-25	25 ns	
MSM521209-30	30 ns	

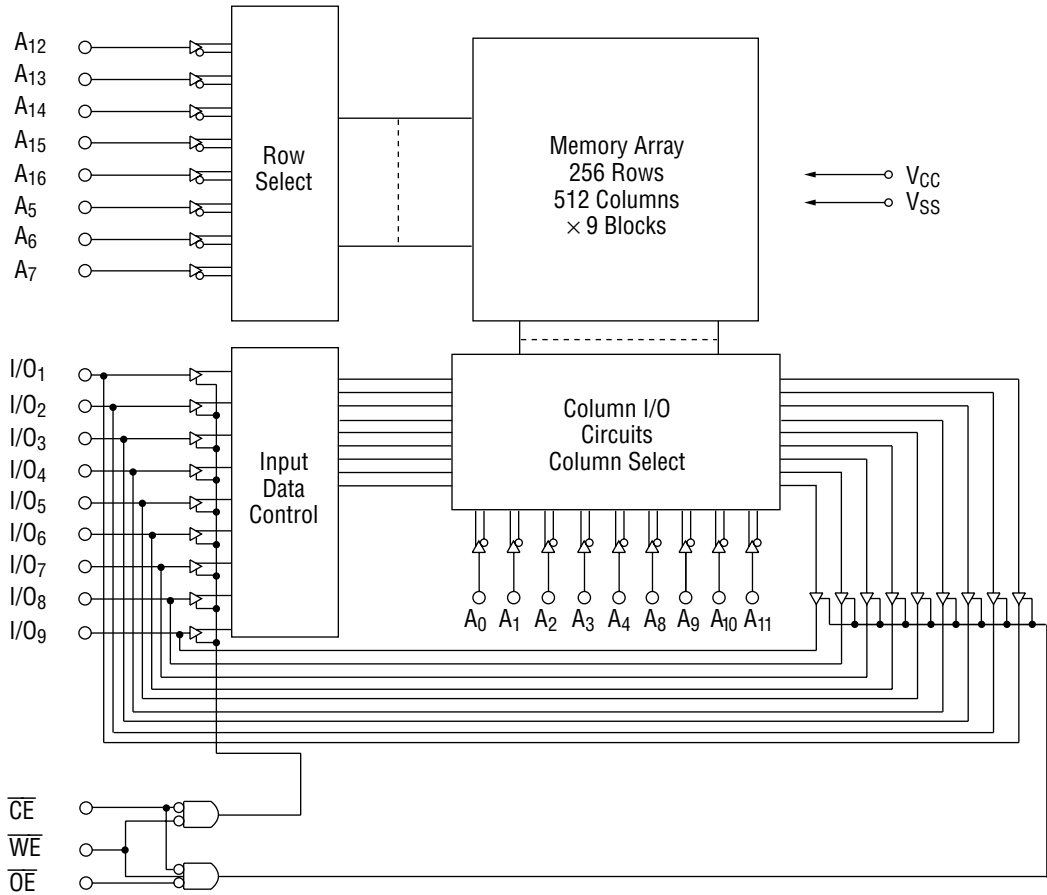
PIN CONFIGURATION (TOP VIEW)



36-Pin Plastic SOJ

Pin Name	Function
A0 - A16	Address Input
I/O1 - I/O9	Data Input/Output
\overline{CE}	Chip Enable
\overline{OE}	Output Enable
\overline{WE}	Write Enable
V_{CC} , V_{SS}	Power Supply
NC	No Connection

BLOCK DIAGRAM



FUNCTION TABLE

Operating Mode	CE	WE	OE	Operating Contents
Standby	H	*	*	Output Floating
Read Cycle	L	H	H	Output Floating
	L	H	L	Data Read
Write Cycle	L	L	*	Data Write

*Don't Care ("H" or "L")

ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings

Parameter	Symbol	Condition	Rating	Unit
Power Supply Voltage	V_{CC}	$T_a = 25^\circ\text{C}$, for V_{SS}	-0.5 to 4.6	V
Pin Voltage	V_T		-0.5^* to $V_{CC} + 0.5$	V
Power Dissipation	P_D	$T_a = 25^\circ\text{C}$	1.0	W
Operating Temperature	T_{opr}	—	0 to 70	$^\circ\text{C}$
Storage Temperature	T_{stg}	—	-55 to 125	$^\circ\text{C}$

* -2.0 V Min. for pulse width less than 10 ns.

Recommended Operating Conditions

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Power Supply Voltage	V_{CC}	—	3.0	3.3	3.6	V
	V_{SS}		0	0	0	V
Input High Voltage	V_{IH}	$V_{CC} = 3.3\text{ V} \pm 0.3\text{ V}$	2.0	—	$V_{CC} + 0.3$	V
Input Low Voltage	V_{IL}		-0.3^*	—	0.8	V
Load Capacitance	C_L	—	—	—	30	pF

* -2.0 V Min. for pulse width less than 10 ns.

Capacitance

($T_a = 25^\circ\text{C}$, $f = 1\text{ MHz}$)

Parameter	Symbol	Condition	Min.	Max.	Unit
Input Capacitance	C_I	$V_{IN} = 0\text{ V}$	—	8	pF
Input/Output Capacitance	$C_{I/O}$	$V_{I/O} = 0\text{ V}$	—	8	pF

Note: This parameter is periodically sampled and not 100% tested.

DC Characteristics

($V_{CC} = 3.3\text{ V} \pm 0.3\text{ V}$, $T_a = 0^\circ\text{C}$ to 70°C)

Parameter	Symbol	Condition	MSM521209			Unit
			Min.	Typ.	Max.	
Input Leakage Current	I_{LI}	$V_I = 0$ to V_{CC}	-10	—	10	μA
Input/Output Leakage Current	I_{LO}	$\overline{CE} = V_{IH}$ or $\overline{OE} = V_{IH}$, $V_{I/O} = 0$ to V_{CC}	-10	—	10	μA
Output High Voltage	V_{OH}	$I_{OH} = -2\text{ mA}$	2.4	—	—	V
Output Low Voltage	V_{OL}	$I_{OL} = 2\text{ mA}$	—	—	0.4	V
Standby Power Supply Current	I_{CCS}	$\overline{CE} \geq V_{CC} - 0.2\text{ V}$, $V_{IN} \leq 0.2\text{ V}$ or $V_{IN} \geq V_{CC} - 0.2\text{ V}$	—	—	2	mA
	I_{CCS1}	$\overline{CE} = V_{IH}$, Min. cycle	—	—	35	mA
Operating Power Supply Current	I_{CCA}	Min. cycle, $I_{OUT} = 0\text{ mA}$	—	—	①	mA

① 521209-20 200 mA
 521209-25 180 mA
 521209-30 160 mA

AC Characteristics

Test Conditions

Parameter	Condition
Input Pulse Level	$V_{IH} = 3\text{ V}$, $V_{IL} = 0\text{ V}$
Input Rise and Fall Times	3 ns
Input/Output Timing Level	1.4 V
Output Load	See Figures

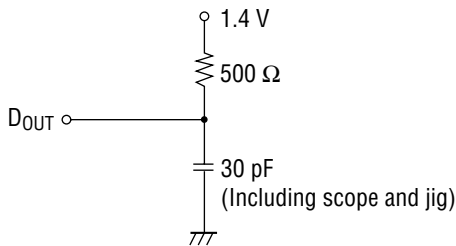


Figure 1 Output Load

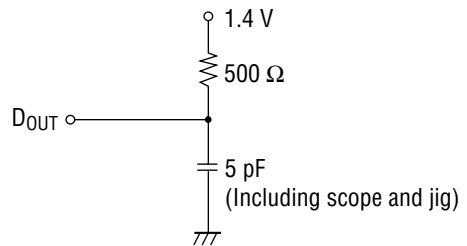


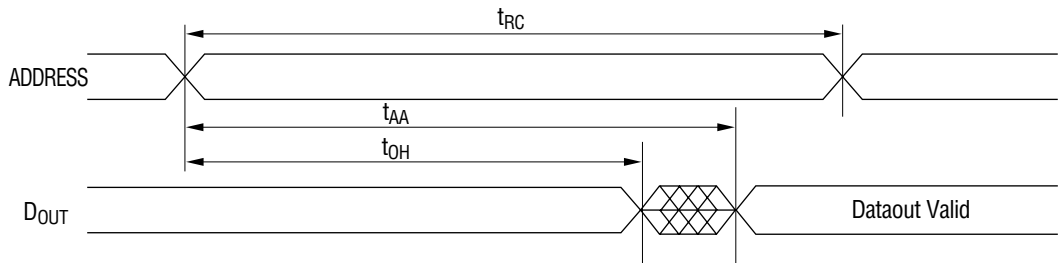
Figure 2 Output Load
 (t_{OLZ} , t_{CLZ} , t_{OHZ} , t_{CHZ} , t_{WLZ} , t_{WHZ})

Read Cycle

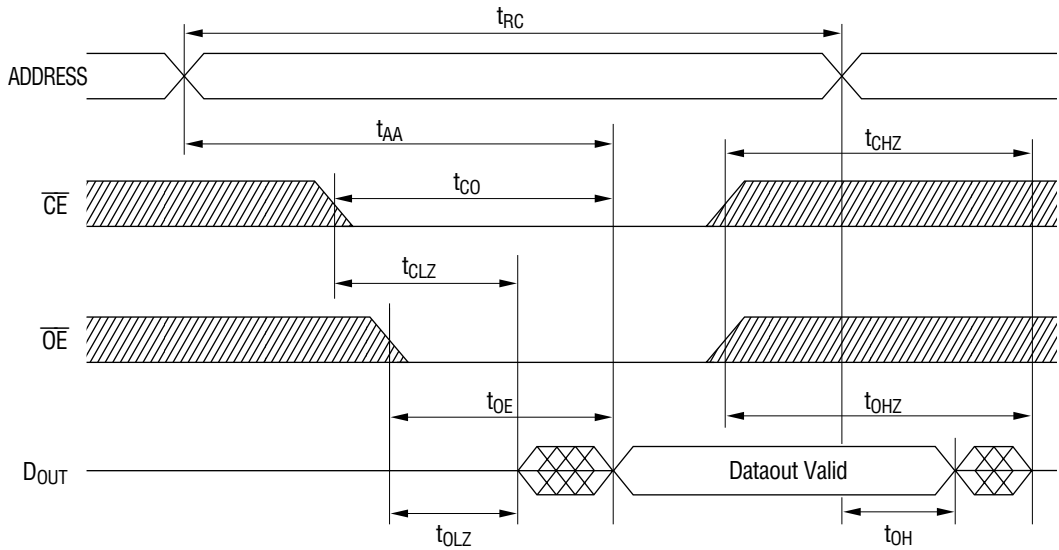
($V_{CC} = 3.3\text{ V} \pm 0.3\text{ V}$, $T_a = 0^\circ\text{C}$ to 70°C)

Parameter	Symbol	MSM521209-20		MSM521209-25		MSM521209-30		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	
Read Cycle Time	t_{RC}	20	—	25	—	30	—	ns
Address Access Time	t_{AA}	—	20	—	25	—	30	ns
\overline{CE} Access Time	t_{CO}	—	20	—	25	—	30	ns
\overline{OE} Access Time	t_{OE}	—	10	—	12	—	15	ns
\overline{CE} to Output in Low-Z	t_{CLZ}	3	—	3	—	3	—	ns
\overline{OE} to Output in Low-Z	t_{OLZ}	0	—	0	—	0	—	ns
Output Hold Time from Address Change	t_{OH}	5	—	5	—	5	—	ns
\overline{CE} to Output in High-Z	t_{CHZ}	—	8	—	10	—	12	ns
\overline{OE} to Output in High-Z	t_{OHZ}	—	8	—	10	—	12	ns

Address Controlled Read ($\overline{WE} = H$, $\overline{CE} = L$, $\overline{OE} = L$)



\overline{CE} , \overline{OE} Controlled Read ($\overline{WE} = H$)



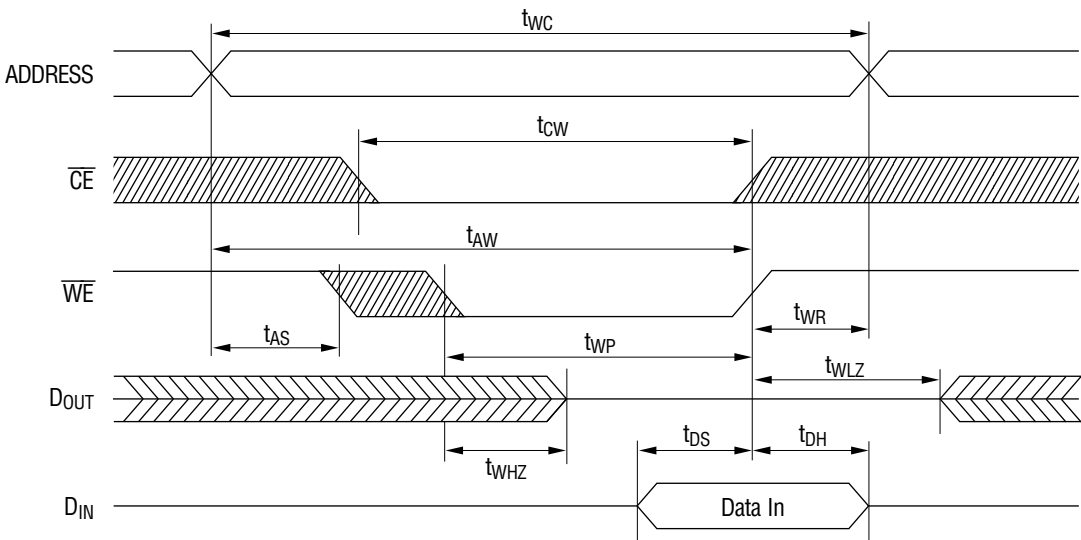
- Notes :
1. A read cycle occurs during the overlap of $\overline{CE} = "L"$, $\overline{OE} = "L"$ and $\overline{WE} = "H"$.
 2. t_{CHZ} and t_{OHZ} are specified by the time when DATA is floating, not defined by the output level.

Write Cycle

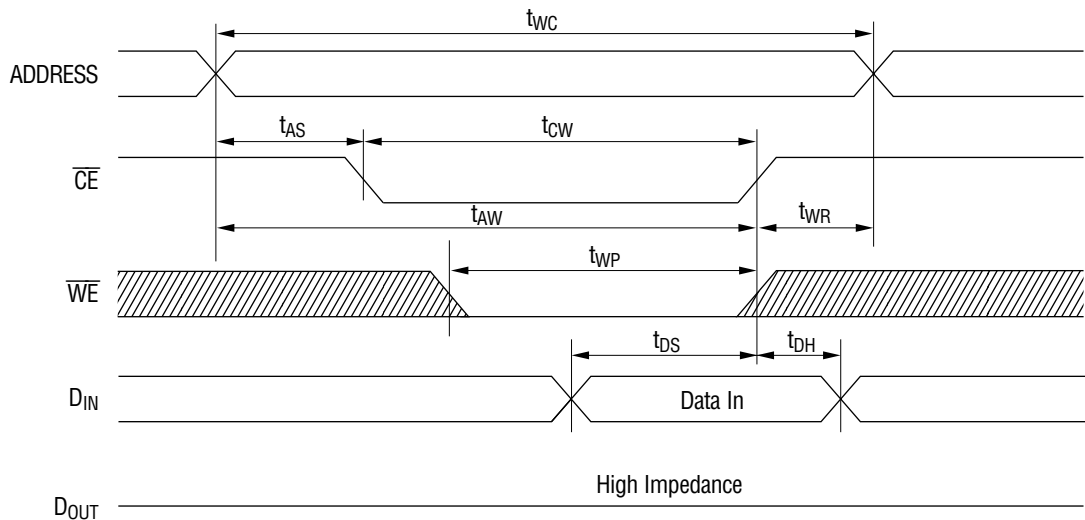
($V_{CC} = 3.3\text{ V} \pm 0.3\text{ V}$, $T_a = 0^\circ\text{C}$ to 70°C)

Parameter	Symbol	MSM521209-20		MSM521209-25		MSM521209-30		Unit	
		Min.	Max.	Min.	Max.	Min.	Max.		
Write Cycle Time	t_{WC}	20	—	25	—	30	—	ns	
Address Setup Time	t_{AS}	0	—	0	—	0	—	ns	
Write Pulse Width	t_{WP}	15	—	20	—	25	—	ns	
Write Recovery Time	\overline{WE}	t_{WR}	0	—	0	—	0	—	ns
	\overline{CE}		0	—	0	—	0	—	
Data Setup Time	t_{DS}	10	—	12	—	14	—	ns	
Data Hold Time	t_{DH}	0	—	0	—	0	—	ns	
\overline{WE} to Output in High-Z	t_{WHZ}	—	8	—	10	—	12	ns	
\overline{CE} to End of Write	t_{CW}	15	—	20	—	25	—	ns	
Address Valid to End of Write	t_{AW}	15	—	20	—	25	—	ns	
Output Active from End of Write	t_{WLZ}	0	—	0	—	0	—	ns	

\overline{WE} Controlled Write ($\overline{OE} = L$)



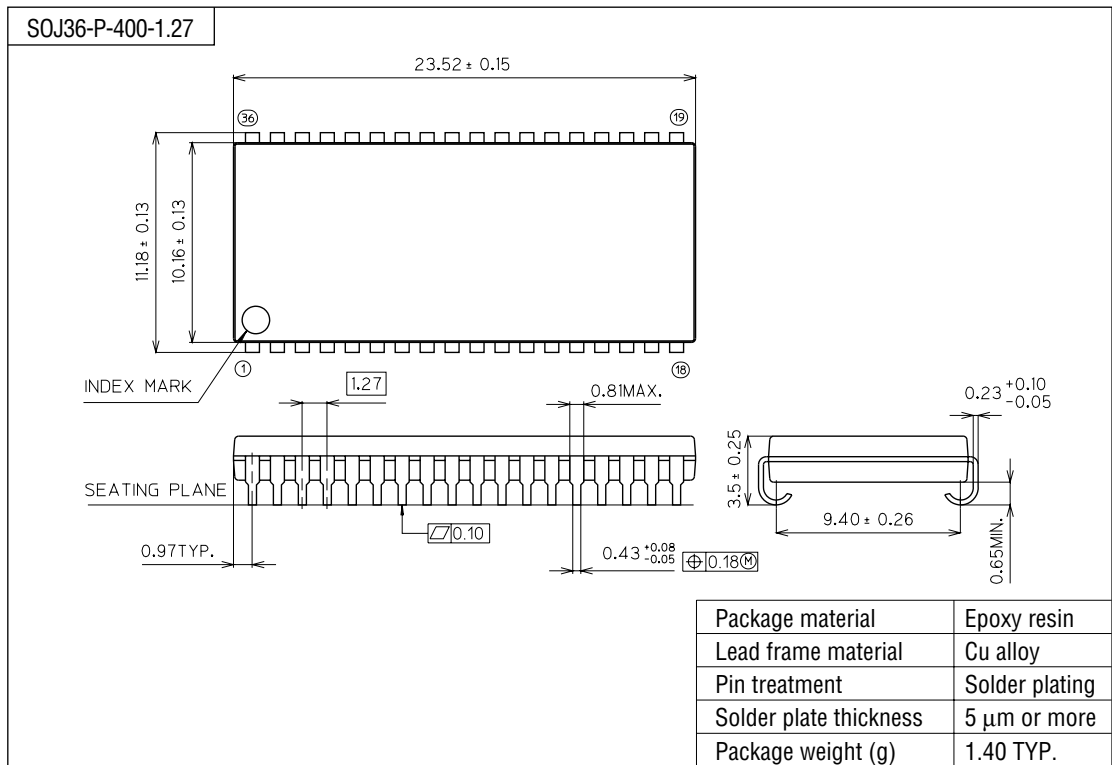
\overline{CE} Controlled Write ($\overline{OE} = H$)



- Notes:
1. A write cycle occurs during the overlap of $\overline{CE} = "L"$ and $\overline{WE} = "L"$.
 2. \overline{OE} may be either of "H" or "L" in the write cycle.
 3. t_{AS} is specified from $\overline{CE} = "L"$ or $\overline{WE} = "L"$, whichever occurs last.
 4. t_{WP} is an overlap time of $\overline{CE} = "L"$ and $\overline{WE} = "L"$.
 5. t_{WR} , t_{DS} and t_{DH} are specified from $\overline{CE} = "H"$ or $\overline{WE} = "H"$, whichever occurs first.
 6. t_{WHZ} is specified by the time when DATA output is floating, not defined by the output level.
 7. When I/O pins are in the output mode, don't apply the inverted input signal to the output pins.

PACKAGE DIMENSIONS

(Unit : mm)



Notes for Mounting the Surface Mount Type Package

The SOP, QFP, TSOP, SOJ, QFJ (PLCC), SHP and BGA are surface mount type packages, which are very susceptible to heat in reflow mounting and humidity absorbed in storage. Therefore, before you perform reflow mounting, contact Oki's responsible sales person for the product name, package name, pin number, package code and desired mounting conditions (reflow method, temperature and times).